

DOUBLE-DIODE PENTODE with variable mutual conductance for use as R.F., I.F. and A.F. amplifier

DOUBLE-DIODE-PENTHODE à pente variable pour utilisation en amplificatrice H.F., M.F. et B.F.

DOPPELDIODE-PENTODE mit veränderlicher Steilheit zur Verwendung als HF-, ZF- und NF-Verstärker

Heating : indirect by A.C. or D.C.; series or parallel supply

Chauffage: indirect par C.A. ou C.C.; alimentation en parallèle ou en série

Heizung : indirekt durch Wechsel- oder Gleichstrom; Serien- oder Parallelspeisung

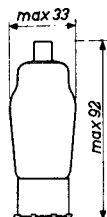
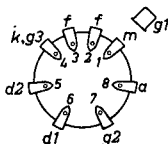
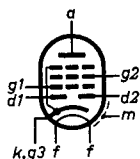
$V_f = 6,3 \text{ V}$

$I_f = 0,2 \text{ A}$

Dimensions in mm

Dimensions en mm

Abmessungen in mm



Base, culot, Sockel: P

Capacitances

Capacités

Kapazitäten

| | | | | | |
|------------|---|----------|-----------------|---|-----------|
| C_{g1} | = | 4,4 pF | C_{d1g1} | < | 0,0005 pF |
| C_a | = | 8,6 pF | C_{d2g1} | < | 0,0005 pF |
| C_{ag1} | < | 0,002 pF | $C_{(d1+d2)g1}$ | < | 0,001 pF |
| C_{g1f} | < | 0,01 pF | C_{d1a} | < | 0,3 pF |
| C_{d1} | = | 3 pF | C_{d2a} | < | 0,25 pF |
| C_{d2} | = | 3 pF | $C_{(d1+d2)a}$ | < | 0,4 pF |
| C_{d1d2} | < | 0,3 pF | | | |

Operating characteristics of the pentode section
 Caractéristiques d'utilisation de la partie penthode
 Betriebsdaten des Pentodenteiles

| | | | | | | | |
|----------|---|------|-------|------|-------|------|----------------|
| V_a | = | 100 | | 200 | | 250 | V |
| R_{g2} | = | - | | 60 | | 95 | k Ω |
| R_k | = | 300 | | 300 | | 300 | Ω |
| V_{g1} | = | -2 | -16,5 | -2 | -32,5 | -2 | -38 V |
| V_{g2} | = | 100 | 100 | 100 | 200 | 100 | 250 V |
| I_a | = | 5 | - | 5 | - | 5 | mA |
| I_{g2} | = | 1,6 | - | 1,6 | - | 1,6 | mA |
| S | = | 1800 | 18 | 1800 | 18 | 1800 | 18 μ A/V |
| R_1 | = | 0,4 | >10 | 1,0 | >10 | 1,3 | >10 M Ω |

Limiting values of the pentode section
 Caractéristiques limites de la partie penthode
 Grenzdaten des Pentodenteiles

| | | |
|-------------------------------------|--------|---------------|
| V_{a0} | = max. | 550 V |
| V_a | = max. | 300 V |
| W_a | = max. | 1,5 W |
| V_{g20} | = max. | 550 V |
| V_{g2} ($I_a = 5$ mA) | = max. | 125 V |
| V_{g2} ($I_a < 2$ mA) | = max. | 300 V |
| W_{g2} | = max. | 0,3 W |
| I_k | = max. | 10 mA |
| V_{g1} ($I_{g1} = +0,3$ μ A) | = max. | -1,3 V |
| R_{g1} | = max. | 3 M Ω |
| R_{kf} | = max. | 20 k Ω |
| V_{kf} | = max. | 100 V |

Limiting values of the diode section (each section)
 Caractéristiques limites de la partie diode
 (par système)
 Grenzdaten des Diodenteiles (pro System)

| | | |
|------------------------|--------|---------------|
| V_d inv _p | = max. | 350 V |
| I_d | = max. | 0,8 mA |
| I_{d_p} | = max. | 5 mA |
| R_{kf} | = max. | 20 k Ω |
| V_{kf} | = max. | 100 V |

PHILIPS



*Electronic
Tube*

HANDBOOK

| page | EBF2 sheet | date |
|-------------|-----------------------|-------------|
| 1 | 1 | 1953.04.04 |
| 2 | 2 | 1953.04.04 |
| 3 | FP | 1999.06.15 |